



PMB087T060SS-255A

5A/60V⁽¹⁾, low VF Planar MOS barrier diode

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	2210 μ m	87.0 mil
	Top Metal Pad Size (B)	2090 μ m	82.3mil
	Chip Size (C)	/	/
	Wafer Thickness (D)	255 μ m	10.0 mil
	Scribe Line Width (E)	80 μ m	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	AG	
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23 $^{\circ}$ C \pm 3 $^{\circ}$ C)	

Electrical Characteristics (T_J=25 $^{\circ}$ C, unless otherwise specified) ⁽²⁾

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{BR}	Reverse Breakdown Voltage	62	68	-	V	I _R =300 μ A
V _F	Instantaneous Forward Voltage	-	0.43	0.47	V	I _F =5A ⁽³⁾
I _R	Reverse Leakage Current	-	80	150	μ A	V _R =60V
T _J , T _{STG}	Operating and Storage Temperature	-40 $^{\circ}$ C to 150 $^{\circ}$ C Max				

Note:

(1) The preliminary wafer datasheet only for reference;

(2) This characteristics assumes the dies are assembled in TO-220 packages. Actual performance may degrade when assembled.

YJ does not guarantee device performance after assembly;

(3) Pulse Width t_p = < 300 μ S, Duty Cycle <2%;